

TOSHIBA Field Effect Transistor Silicon P Channel Junction Type

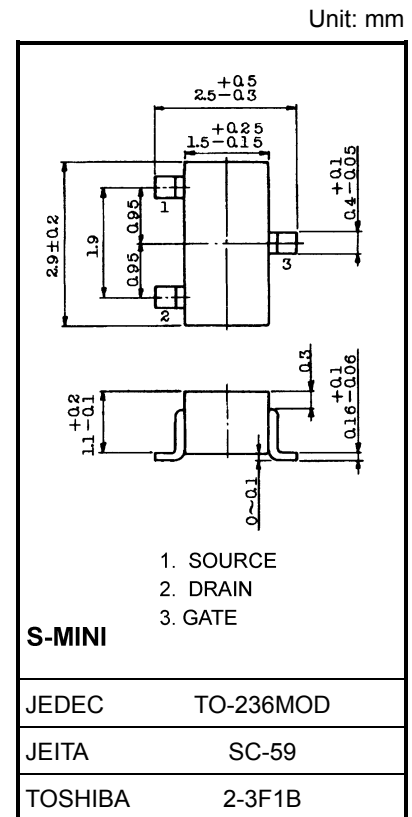
# 2SJ106

- Audio Frequency Amplifier Applications
- Analog Switch Applications
- Constant Current Applications
- Impedance Converter Applications

- High breakdown voltage:  $V_{GDS} = 50\text{ V}$
- High input impedance:  $I_{GSS} = 1.0\text{ nA (max)}$  ( $V_{GS} = 30\text{ V}$ )
- Low  $R_{DS(ON)}$ :  $R_{DS(ON)} = 270\ \Omega$  (typ.) ( $I_{DSS} = -5\text{ mA}$ )
- Small package

### Maximum Ratings ( $T_a = 25^\circ\text{C}$ )

Characteristics	Symbol	Rating	Unit
Gate-drain voltage	$V_{GDS}$	50	V
Gate current	$I_G$	-10	mA
Drain power dissipation	$P_D$	150	mW
Junction temperature	$T_j$	125	$^\circ\text{C}$
Storage temperature range	$T_{stg}$	-55~125	$^\circ\text{C}$



Weight: 0.012 g (typ.)

### Electrical Characteristics ( $T_a = 25^\circ\text{C}$ )

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Gate cut-off current	$I_{GSS}$	$V_{GS} = 30\text{ V}, V_{DS} = 0$	—	—	1.0	nA
Gate-drain breakdown voltage	$V_{(BR)GDS}$	$V_{DS} = 0, I_G = 100\ \mu\text{A}$	50	—	—	V
Drain current	$I_{DSS}$ (Note)	$V_{DS} = -10\text{ V}, V_{GS} = 0$	-1.2	—	-14	mA
Gate-source cut-off voltage	$V_{GS(OFF)}$	$V_{DS} = -10\text{ V}, I_D = -0.1\ \mu\text{A}$	0.3	—	6.0	V
Forward transfer admittance	$ Y_{fs} $	$V_{DS} = -10\text{ V}, V_{GS} = 0, f = 1\text{ kHz}$	1.0	4.0	—	mS
Drain-source on resistance	$R_{DS(ON)}$	$V_{DS} = -10\text{ mV}, V_{GS} = 0$ $I_{DSS} = -5\text{ mA}$	—	270	—	$\Omega$
Input capacitance	$C_{iss}$	$V_{DS} = -10\text{ V}, V_{GS} = 0, f = 1\text{ MHz}$	—	18	—	pF
Reverse transfer capacitance	$C_{rss}$	$V_{DG} = -10\text{ V}, I_D = 0, f = 1\text{ MHz}$	—	3.6	—	pF

Note:  $I_{DSS}$  classification Y: -1.2~-3.0 mA, GR (G): -2.6~-6.5 mA, BL (L): -6~-14 mA

### Marking

